Growth of crystalline $\text{Gd}_3\text{Ga}_5\text{O}_{12}$ thin-film optical waveguides by pulsed laser deposition

Devinder S. Gill and Robert W. Eason

Optoelectronics Research Centre and Department of Physics
University of Southampton, Southampton, SO17 1BJ, United Kingdom
Tel. +44 703 594527, FAX +44 703 593142, email dsg@orc.soton.ac.uk

Jesus Mendiola

Instituto de Ciencia de Materiales de Madrid
Consejo Superior de Investigaciones Científicas,
Campus Universitario de Cantoblanco C-IV, 28049 Madrid, Spain
Tel. +34 1 3974783, FAX +34 1 3978579

Peter Chandler

School of Mathematical and Physical Sciences,
University of Sussex, Brighton, BN1 9QH, United Kingdom.
Tel. +44 273 606755, FAX +44 273 678097

Abstract

Crystalline and stoichiometric thin films of $\text{Gd}_3\text{Ga}_5\text{O}_{12}$ have been deposited onto heated $\text{Y}_3\text{Al}_5\text{O}_{12}$ substrates by a pulsed laser deposition technique. The refractive indices of the films are in excellent agreement with the bulk crystal.
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Summary
Optical waveguides of laser gain media are highly desirable because the high intensity-length product and good pump-signal mode overlap, which can be achieved in the waveguide geometry, leads to a reduced threshold pump power as compared to bulk lasers. Although optical waveguides of Gd$_3$Ga$_5$O$_{12}$ (GGG) have been fabricated by ion-implantation of the GGG crystal$^1$, the technique is very expensive and a cheaper and simpler alternative is the pulsed laser deposition (PLD) technique. To our knowledge, the successful growth of crystalline laser-host thin films by PLD has
not been previously reported.

The experimental arrangement for the PLD of thin films is shown in figure 1. The cylindrical GGG single-crystal target was ablated along its length using a KrF excimer laser beam (\( \lambda = 248 \text{nm} \)) with an incident laser fluence of \( \approx 5 \text{J/cm}^2 \). A \( \text{Y}_3\text{Al}_5\text{O}_{12} \) (YAG) substrate was positioned 2.5 cm away from the target and heated on its front surface to a maximum temperature of 750°C with a 10W \( \text{CO}_2 \) laser beam. Deposition was carried out in a vacuum chamber, at a background pressure of \( \approx 10^{-5} \text{mbar} \) and then backfilled with an oxygen partial pressure ranging from \( 1.2 \times 10^{-2} \text{mbar} \) to \( 1.9 \text{mbar} \) just prior to ablation.

The stoichiometry of the GGG thin films was investigated using Rutherford backscattering spectroscopy (RBS). The solid line in fig. 2 corresponds to the computer simulation of a \( \text{Gd}_3\text{Ga}_5\text{O}_{12} \) film which has a close fit with the experimental RBS results.

The crystalline quality of the GGG thin films was investigated with a D-500 Siemens, grazing incidence x-ray diffractometer. Figure 3(a) represents a film grown at 530°C which was completely amorphous with only the (444) YAG substrate peak present. Figs 3(b)-3(d) show that as the substrate temperature was increased, the (444) GGG peak appeared which was progressively sharper, implying improved crystallinity at elevated temperatures. The (444) GGG peak in fig 3(d) was located at a d-spacing of 1.798 Å so that the lattice spacing difference between the film and bulk crystal of GGG was only 0.6%. In all the x-ray spectra, no other diffraction peaks were identified implying that the GGG had grown exclusively in the highly-oriented (444) plane parallel to the (444) YAG surface.

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Finally, the waveguiding properties of the GGG film shown in figure 3(d) were investigated by coupling light from a He-Ne laser at 633nm into the layer using a rutile prism. The refractive index of the layer was calculated to be 1.972 which is in excellent agreement with the bulk crystal value of 1.965.

Current work involves in-situ doping of the films with Nd ions to obtain some fluorescence data for further laser waveguide studies.
References


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Figure Captions

1) Experimental arrangement used for PLD and heating the YAG substrate with a CO₂ laser.

2) Rutherford backscattering spectra of a film grown on a (444) oriented YAG single-crystal substrate. The solid line represents the experimental results and the dotted line represents the fit assuming a film with a composition of Gd₃Ga₅O₁₂.

3) X-ray diffraction spectra of the films formed on (444) YAG single-crystal substrates at an oxygen partial pressure of ≈10⁻² mbar and (a) a substrate temperature of 530°C, (b) a substrate temperature of 650°C, (c) a substrate temperature of 685°C and (d) a substrate temperature of 750°C. The dashed line corresponds to the diffraction angle of the (444) YAG substrate peak at 2θ = 52.8°.